Appl. No. 10/666,034 Amdt. dated July 18, 2005 Response to Notice of Allowance June 6, 2005

Amendments to the Abstract:

Please replace the Abstract paragraph with the following amended Abstract:

A semiconductor device is disclosed. The semiconductor device includes one or more charge control electrodes a plurality of charge control electrodes. The one or more charge control electrodes may control the electric field within the drift region of a semiconductor device. A semiconductor device is formed as follows. A semiconductor substrate having a first region of a first conductivity type is provided. A region of a second conductivity type is formed in the semiconductor substrate such that the first and second regions form a p-n junction. First and second charge control electrodes are formed adjacent to but insulated from one of the first and second regions, along a dimension parallel to flow of current through the semiconductor device, wherein the first charge control electrode is adapted to be biased differently than the second charge control electrode.